

Power management (dual transistors)

EMF19 / UMF19N

2SC4617 and DTC123EE are housed independently in a EMT or UMT package.

●Application

Power management circuit

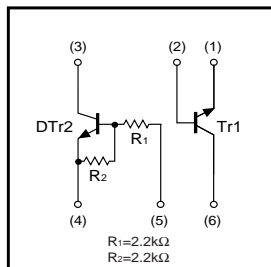
●Features

- 1) Power switching circuit in a single package.
- 2) Mounting cost and area can be cut in half.

●Structure

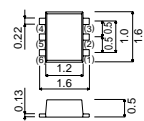
Silicon epitaxial planar transistor

●Equivalent circuits



●External dimensions (Units : mm)

EMF19

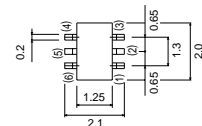


Each lead has same dimensions

ROHM : EMT6

Abbreviated symbol : F19

UMF19N



Each lead has same dimensions

ROHM : UMT6
EIAJ : SC-88

Abbreviated symbol : F19

●Packaging specifications

| Type | EMF19 | UMF19N |
|-----------------------------|-------|--------|
| Package | EMT6 | UMT6 |
| Marking | F19 | F19 |
| Code | T2R | TR |
| Basic ordering unit(pieces) | 8000 | 3000 |

Transistors

●Absolute maximum ratings (Ta=25°C)

Tr1

| Parameter | Symbol | Limits | Unit |
|---------------------------|------------------|-------------|------|
| Collector-base voltage | V _{CB0} | 60 | V |
| Collector-emitter voltage | V _{CEO} | 50 | V |
| Emitter-base voltage | V _{EBO} | 7 | V |
| Collector current | I _C | 150 | mA |
| Power dissipation | P _C | 150 (TOTAL) | mW* |
| Junction temperature | T _J | 150 | °C |
| Storage temperature | T _{stg} | -55~+150 | °C |

* 120mW per element must not be exceeded.

DTr2

| Parameter | Symbol | Limits | Unit |
|------------------------------|------------------|------------|-------|
| Supply voltage | V _{CC} | 50 | V |
| Input voltage | V _{IN} | -10~+20 | V |
| Collector current | I _C | 100 | mA *1 |
| Output current | I _O | 100 | mA |
| Power dissipation | P _C | 150(TOTAL) | mW *2 |
| Junction temperature | T _J | 150 | °C |
| Range of storage temperature | T _{stg} | -55~+150 | °C |

*1 Characteristics of built-in transistor.

*2 120mW per element must not be exceeded.
Each terminal mounted on a recommended land.

●Electrical characteristics (Ta=25°C)

Tr1

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------------------|----------------------|------|------|------|------|--|
| Collector-base breakdown voltage | BV _{CB0} | 60 | - | - | V | I _C =50μA |
| Collector-emitter breakdown voltage | BV _{CEO} | 50 | - | - | V | I _C =1mA |
| Emitter-base breakdown voltage | BV _{EBO} | 7 | - | - | V | I _E =50μA |
| Collector cutoff current | I _{CB0} | - | - | 0.1 | μA | V _{CB} =60V |
| Emitter cutoff current | I _{EBO} | - | - | 0.1 | μA | V _{EB} =7V |
| Collector-emitter saturation voltage | V _{CE(sat)} | - | - | 0.4 | V | I _C /I _B =50mA/5mA |
| DC current transfer ratio | h _{FE} | 180 | - | 390 | - | V _{CE} =6V, I _C =1mA |
| Transition frequency | f _T | - | 180 | - | MHz | V _{CE} =12V, I _E =-2mA, f=100MHz |
| Output capacitance | C _{ob} | - | 2 | 3.5 | PF | V _{CB} =12V, I _E =0A, f=1MHz |

DTr2

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|----------------------|--------------------------------|------|------|------|------|--|
| Input voltage | V _{I(off)} | - | - | 0.5 | V | V _{CC} =5V, I _O =100μA |
| | V _{I(on)} | 3.0 | - | - | V | V _O =0.3V, I _O =20mA |
| Output voltage | V _{O(on)} | - | 100 | 300 | mV | V _O =10mA, I _I =0.5mA |
| Input current | I _I | - | - | 3.8 | mA | V _I =5V |
| Output current | I _{O(off)} | - | - | 0.5 | μA | V _{CC} =50V, V _I =0V |
| DC current gain | G _I | 20 | - | - | - | V _O =5V, I _O =20mA |
| Transition frequency | f _T | - | 250 | - | MHz | V _{CE} =10V, I _E =-5mA, f=100MHz * |
| Input resistance | R ₁ | 1.54 | 2.2 | 2.86 | kΩ | - |
| Resistance ratio | R ₂ /R ₁ | 0.8 | 1.0 | 1.2 | - | - |

* Characteristics of built-in transistor.

Transistors

●Electrical characteristic curves

Tr1

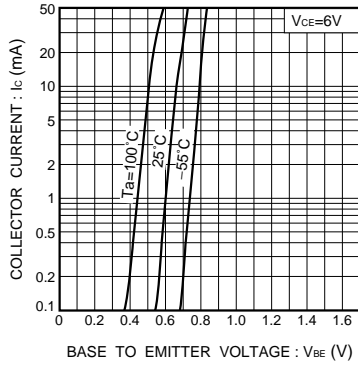


Fig.1 Grounded emitter propagation characteristics

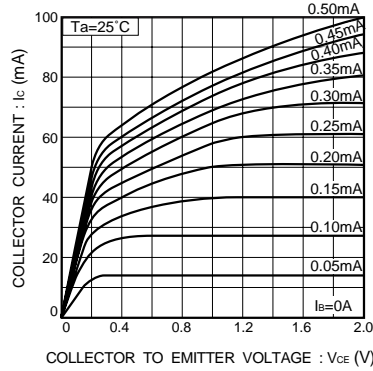


Fig.2 Grounded emitter output characteristics (I)

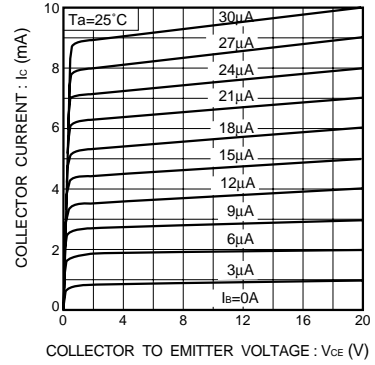


Fig.3 Grounded emitter output characteristics (II)

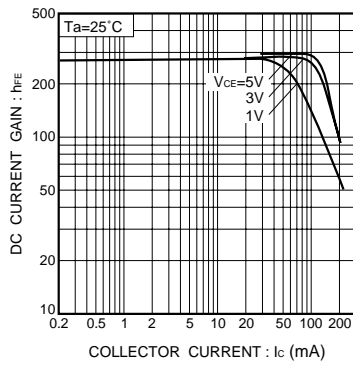


Fig.4 DC current gain vs. collector current (I)

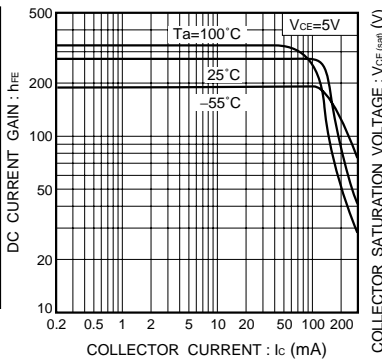


Fig.5 DC current gain vs. collector current (II)

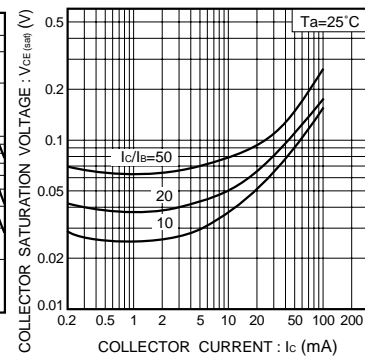


Fig.6 Collector-emitter saturation voltage vs. collector current

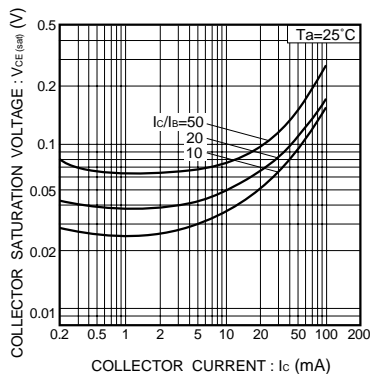


Fig.7 Collector-emitter saturation voltage vs. collector current (I)

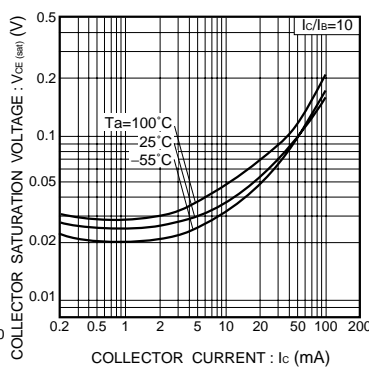


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

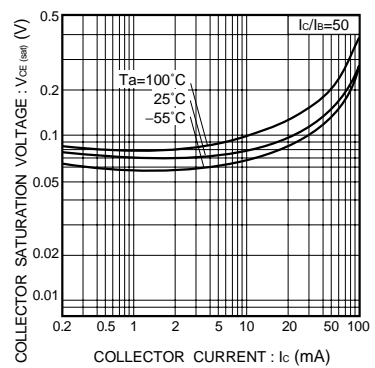


Fig.9 Collector-emitter saturation voltage vs. collector current (III)

Transistors

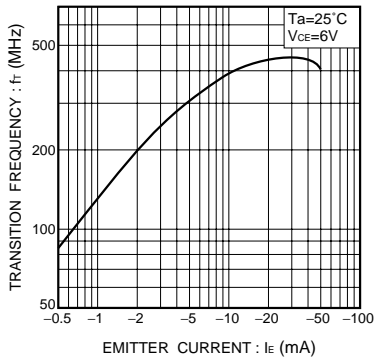


Fig.10 Gain bandwidth product vs. emitter current

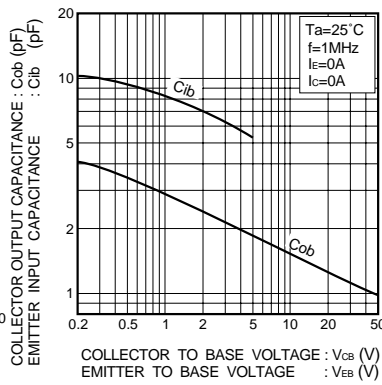


Fig.11 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

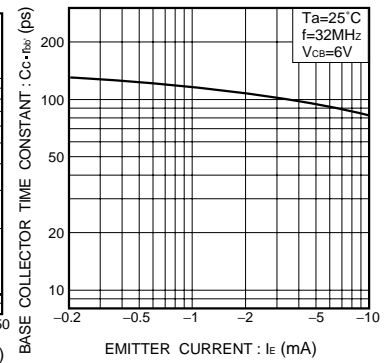


Fig.12 Base-collector time constant vs. emitter current

DTr2

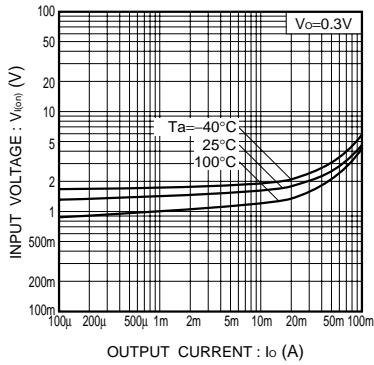


Fig.9 Input voltage vs. output current (ON characteristics)

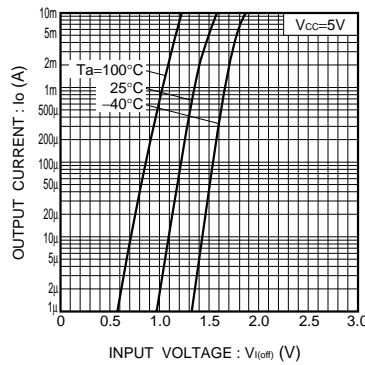


Fig.10 Output current vs. input voltage (OFF characteristics)

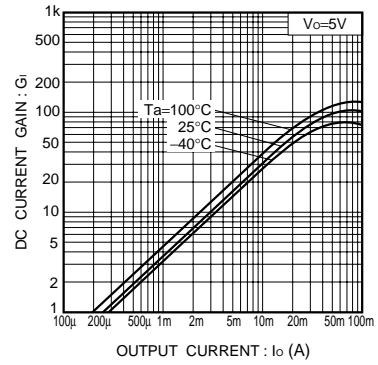


Fig.11 DC current gain vs. output current

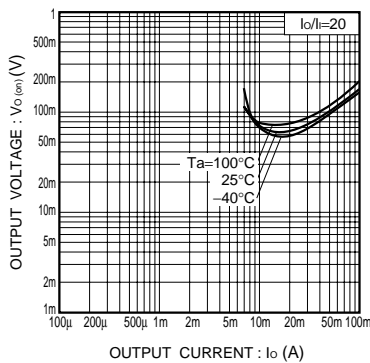


Fig.12 Output voltage vs. output current

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